AMENDMENTS TO THE SPECIFICATION

Please amend the specification at page 10 by replacing the paragraph beginning at line 21 with the following amended paragraph:

G1

Fig. 2 presents a cross sectional view of a field effect transistor 50 formed by the method of the present invention. The field effect transistor 50 is formed on a semiconductor substrate 52, which is desirably silicon dioxide, quartz or glass. The field effect transistor 50 includes a gate oxide 54, a source 56 and a drain 58. The gate oxide 54, the source 56 and the drain 58 are formed [[in]] on the substrate 52. A layer 64 of polysilicon 66 is formed on the gate oxide 54 to form a gate electrode 70. A pair of spacers 68 is formed on the sides of the layer 64 of polysilicon 66. A layer 72 of a field oxide 74 is also formed on the substrate 52.

Please amend the specification at page 13 by replacing the paragraph beginning at line 2 with the following amended paragraph:

G2

A thin film transistor 200 is shown in cross section in Fig. [[3]] 5. The thin film transistor 200 includes an insulating substrate 202. A layer 204 of a semiconducting material 206 is formed on the surface of the substrate 202. A source region 208 and a drain region 210 are formed on the layer 204 of semiconducting material 206. A layer 212 of a dielectric material 214 is formed on the layer 204 of semiconducting material 206 and covers the source 208 and the drain 210. A layer 216 of a conducting material 218 is formed on the layer 212 of dielectric material 214 to form a gate electrode 220.